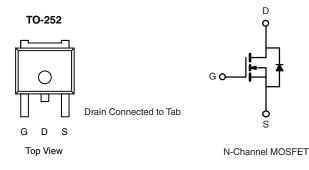


Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.014				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 V$	0.017				
I _D (A)	40				
Configuration	Single				



FEATURES

- TrenchFET[®] Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified^d
- 100 % Rg and UIS Tested
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD40N06-14L-GE3

ABSOLUTE MAXIMUM RATINGS (Г _С = 25 °C, unles	s otherwise noted	(k		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V _{GS} ± 20		- v	
Continuous Drain Current	T _C = 25 °C ^a	1	40		
	T _C = 125 °C	I _D	29		
Continuous Source Current (Diode Conduction) ^a		I _S	40	А	
Pulsed Drain Current ^b		I _{DM}	160		
Single Pulse Avalanche Current		I _{AS}	32		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	51	mJ	
Maria a Dana Distantish	T _C = 25 °C	P	75	W	
Maximum Power Dissipation ^b	T _C = 125 °C	P _D	25	vv	
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to + 175	°C		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	60	°C/W
Junction-to-Case (Drain)		R _{thJC}	2	0/10

Notes

a. Package limited.

b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

c. When mounted on 1" square PCB (FR-4 material).

d. Parametric verification ongoing.

1



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static		•						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		60	-	-	v	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		2.0	2.5		
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	250		
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	30	-	-	А	
		$V_{GS} = 10 V$	I _D = 20 A	-	0.011	0.014	Ω	
Drain Source On State Desistence?	Р	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.024		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 20 A, T _J = 175 °C	-	-	0.029		
		V _{GS} = 4.5 V	I _D = 20 A, T _J = 25 °C	-	0.014	0.017		
Forward Transconductance ^a	9 _{fs}	V _{DS}	= 15 V, I _D = 20 A	-	52	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	1685	2105	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	305	385		
Reverse Transfer Capacitance	C _{rss}]		-	180	225		
Total Gate Charge ^c	Qg			-	34	51	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = 10 V$	$V_{DS} = 30 \text{ V}, I_D = 40 \text{ A}$	-	6	9		
Gate-Drain Charge ^c	Q _{gd}			-	8.5	13		
Gate Resistance	Rg	f = 1 MHz		1.20	2.46	3.70	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	8	12		
Rise Time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = 30 \text{ V}, \ R_{\text{L}} = 0.75 \ \Omega \\ I_{\text{D}} \cong 40 \text{ A}, \ V_{\text{GEN}} = 10 \text{ V}, \ R_{\text{g}} = 1 \ \Omega \end{array}$		-	13	20	- ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	22	33		
Fall Time ^c	t _f			-	9	14		
Source-Drain Diode Ratings and Chara	acteristics ^b	•						
							· ·	
Pulsed Current ^a	I _{SM}			-	-	160	A	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

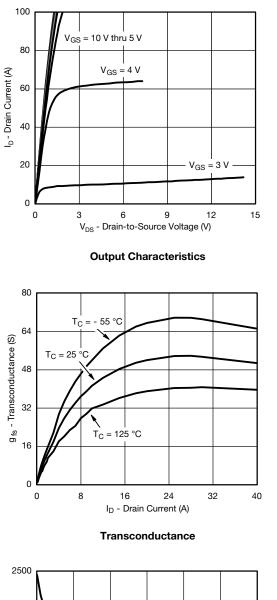
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

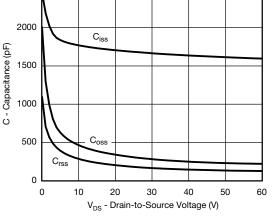
2



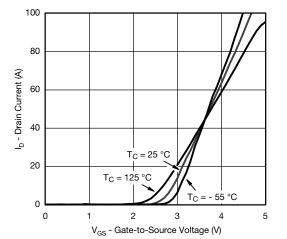
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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

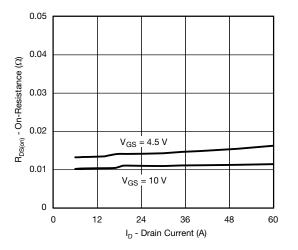


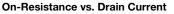


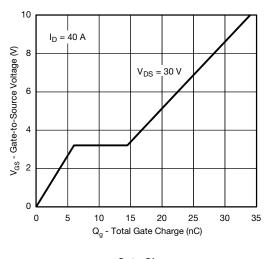
Capacitance



Transfer Characteristics







Gate Charge

S12-1846-Rev. B, 30-Jul-12

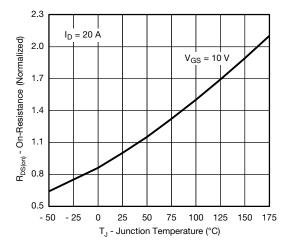
Document Number: 67002

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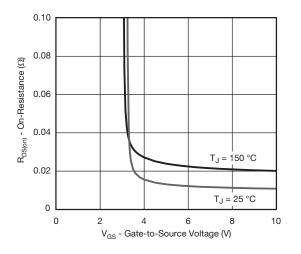


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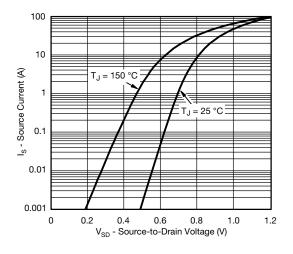
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



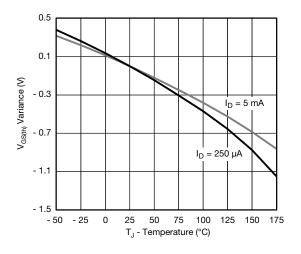
On-Resistance vs. Junction Temperature



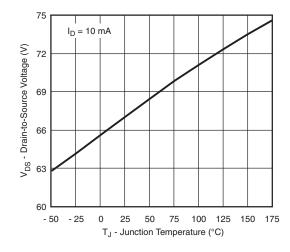
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage







Drain Source Breakdown vs. Junction Temperature

S12-1846-Rev. B, 30-Jul-12

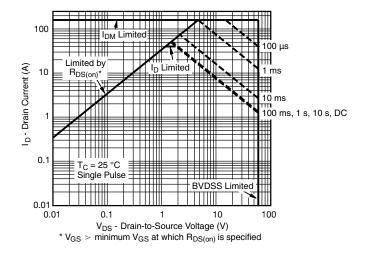
4

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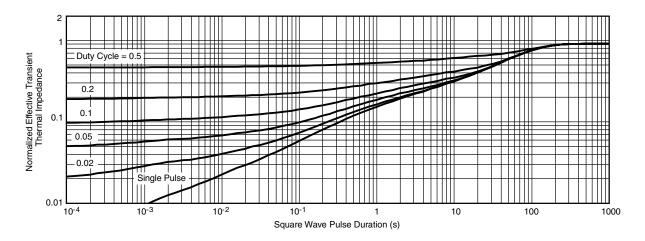


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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



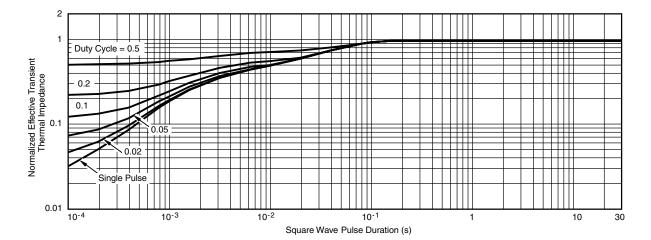
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

The characteristics shown in the two graphs

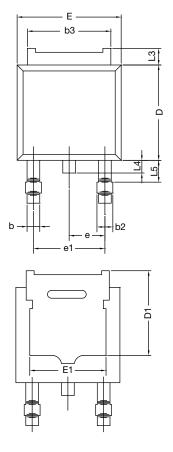
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

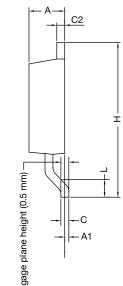
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg267002</u>.





TO-252AA CASE OUTLINE



	MILLIN	IETERS	INCHES			
DIM.	MIN.	MAX.	MIN.	MAX.		
А	2.18	2.38	0.086	0.094		
A1	-	0.127	-	0.005		
b	0.64	0.88	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215		
С	0.46	0.61	0.018	0.024		
C2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245		
D1	5.21	-	0.205	-		
Е	6.35	6.73	0.250	0.265		
E1	4.32	-	0.170	-		
Н	9.40	10.41	0.370	0.410		
е	2.28	BSC	0.090 BSC			
e1	4.56	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070		
L3	0.89	1.27	0.035	0.050		
L4	-	1.02	-	0.040		
L5	1.14	1.52	0.045	0.060		
	ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347					

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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